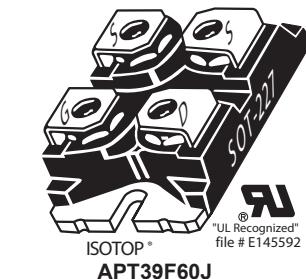
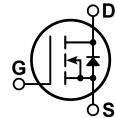


N-Channel FREDFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. This 'FREDFET' version has a drain-source (body) diode that has been optimized for high reliability in ZVS phase shifted bridge and other circuits through reduced t_{rr}, soft recovery, and high recovery dv/dt capability. Low gate charge, high gain, and a greatly reduced ratio of C_{rss}/C_{iss} result in excellent noise immunity and low switching loss. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control di/dt during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency.



Single die FREDFET



FEATURES

- Fast switching with low EMI
- Low t_{rr} for high reliability
- Ultra low C_{rss} for improved noise immunity
- Low gate charge
- Avalanche energy rated
- RoHS compliant 

TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- PFC and other boost converter
- Buck converter
- Single and two switch forward
- Flyback

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
I _D	Continuous Drain Current @ T _C = 25°C	42	A
	Continuous Drain Current @ T _C = 100°C	26	
I _{DM}	Pulsed Drain Current ^①	210	
V _{GS}	Gate-Source Voltage	±30	V
E _{AS}	Single Pulse Avalanche Energy ^②	1580	mJ
I _{AR}	Avalanche Current, Repetitive or Non-Repetitive	28	A

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
P _D	Total Power Dissipation @ T _C = 25°C			480	W
R _{θJC}	Junction to Case Thermal Resistance			0.26	°C/W
R _{θCS}	Case to Sink Thermal Resistance, Flat, Greased Surface		0.15		
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55		150	°C
V _{Isolation}	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			V
W _T	Package Weight		1.03		oz
			29.2		g
Torque	Terminals and Mounting Screws.			10	in·lbf
				1.1	N·m

Static Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

APT39F60J

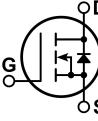
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	600			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D = 250\mu\text{A}$		0.57		$\text{V}/^\circ\text{C}$
$R_{DS(on)}$	Drain-Source On Resistance ^③	$V_{GS} = 10V, I_D = 28\text{A}$		0.09	0.11	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-10		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600V, T_J = 25^\circ\text{C}$			250	μA
		$V_{GS} = 0V, T_J = 125^\circ\text{C}$			1000	
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 30V$			± 100	nA

Dynamic Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	$V_{DS} = 50V, I_D = 28\text{A}$		55		S
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1\text{MHz}$		11300		pF
C_{rss}	Reverse Transfer Capacitance			115		
C_{oss}	Output Capacitance			1040		
$C_{o(cr)}^{\text{④}}$	Effective Output Capacitance, Charge Related	$V_{GS} = 0V, V_{DS} = 0V$ to $400V$		550		pF
$C_{o(er)}^{\text{⑤}}$	Effective Output Capacitance, Energy Related			285		
Q_g	Total Gate Charge	$V_{GS} = 0$ to $10V, I_D = 28\text{A}$, $V_{DS} = 300V$		280		nC
Q_{gs}	Gate-Source Charge			60		
Q_{gd}	Gate-Drain Charge			120		
$t_{d(on)}$	Turn-On Delay Time	Resistive Switching $V_{DD} = 400V, I_D = 28\text{A}$ $R_G = 2.2\Omega^{\text{⑥}}$, $V_{GG} = 15V$		65		ns
t_r	Current Rise Time			75		
$t_{d(off)}$	Turn-Off Delay Time			190		
t_f	Current Fall Time			60		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_s	Continuous Source Current (Body Diode)				42	A
I_{SM}	Pulsed Source Current (Body Diode) ^①				210	
V_{SD}	Diode Forward Voltage	$I_{SD} = 28\text{A}, T_J = 25^\circ\text{C}, V_{GS} = 0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 28\text{A}^{\text{③}}$ $di_{SD}/dt = 100\text{A}/\mu\text{s}$	$T_J = 25^\circ\text{C}$	255	290	ns
Q_{rr}	Reverse Recovery Charge		$T_J = 125^\circ\text{C}$	450	540	
I_{rrm}	Reverse Recovery Current	$V_{DD} = 100V$	$T_J = 25^\circ\text{C}$	1.41		μC
dv/dt	Peak Recovery dv/dt		$T_J = 125^\circ\text{C}$	3.66		
			$T_J = 25^\circ\text{C}$	10.7		A
			$T_J = 125^\circ\text{C}$	15.8		

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at $T_J = 25^\circ\text{C}$, $L = 4.03\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 28\text{A}$.

③ Pulse test: Pulse Width < 380 μs , duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{oss} with $V_{DS} = 67\%$ of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{oss} with $V_{DS} = 67\%$ of $V_{(BR)DSS}$. To calculate $C_{o(er)}$ for any value of V_{DS} less than $V_{(BR)DSS}$, use this equation: $C_{o(er)} = -1.10E-7/V_{DS}^2 + 4.60E-8/V_{DS} + 1.72E-10$.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

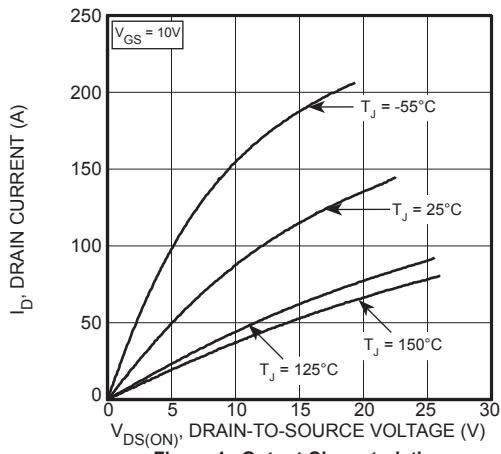


Figure 1, Output Characteristics

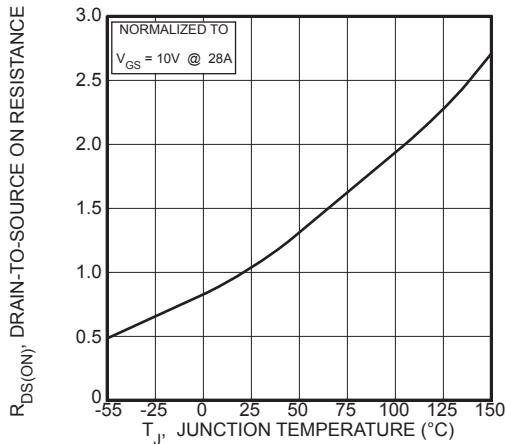
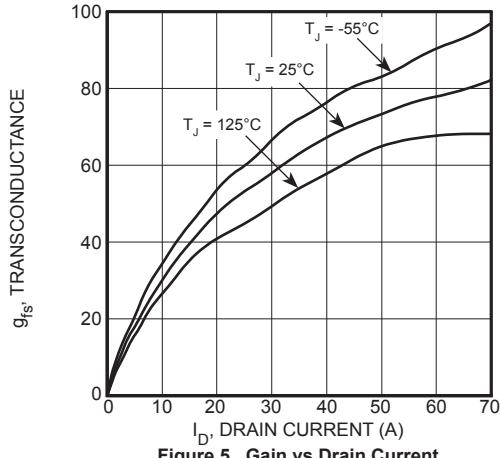
Figure 3, $R_{DS(ON)}$ vs Junction Temperature

Figure 5, Gain vs Drain Current

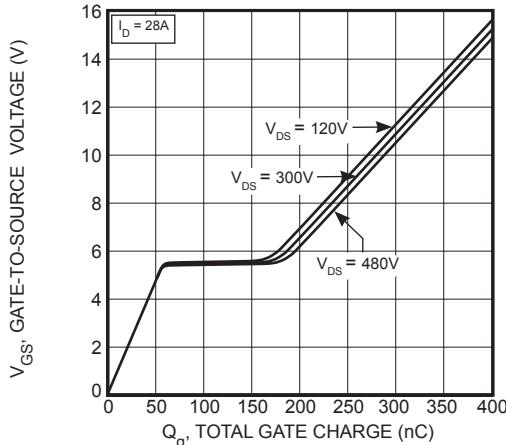


Figure 7, Gate Charge vs Gate-to-Source Voltage

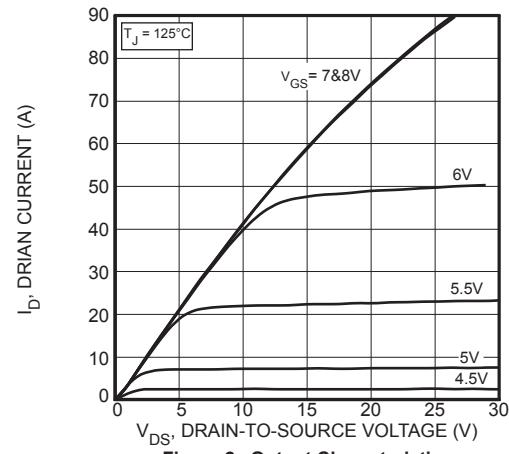


Figure 2, Output Characteristics

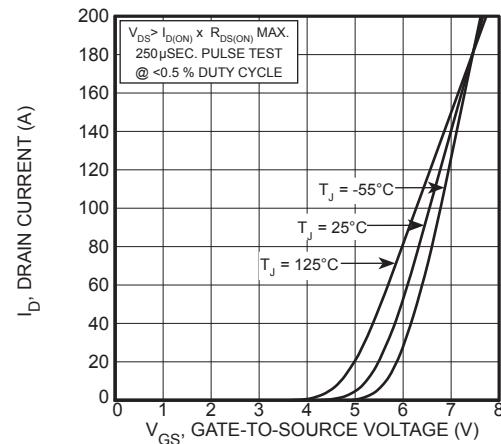


Figure 4, Transfer Characteristics

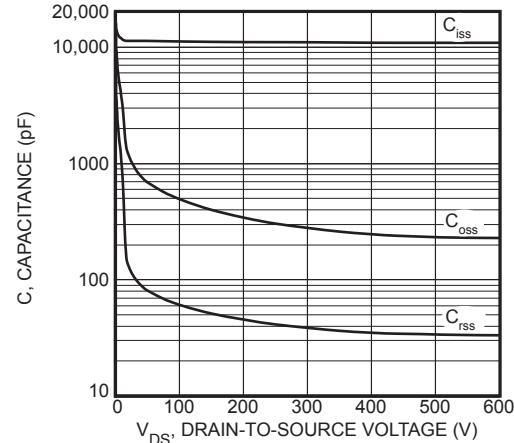


Figure 6, Capacitance vs Drain-to-Source Voltage

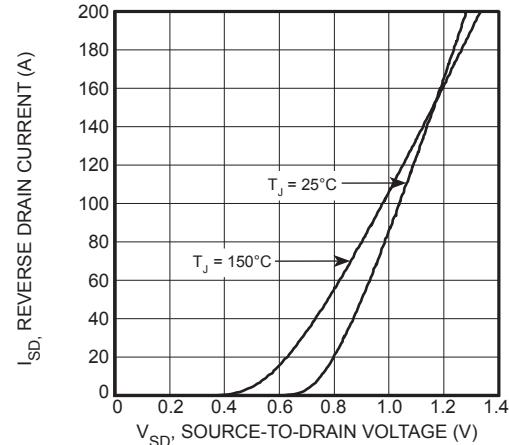


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

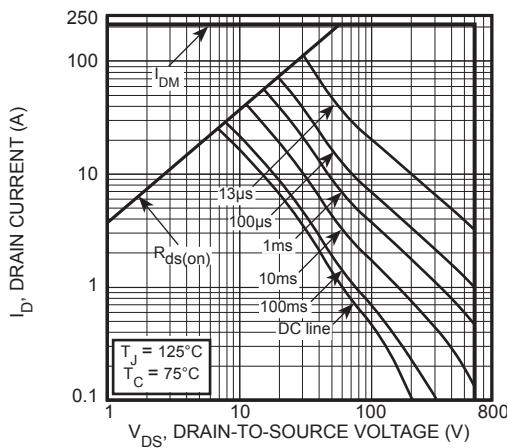


Figure 9, Forward Safe Operating Area

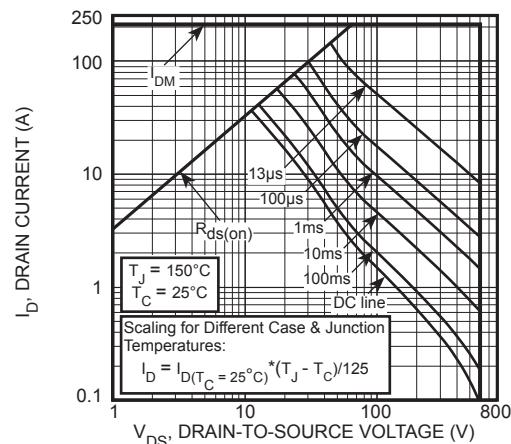


Figure 10, Maximum Forward Safe Operating Area

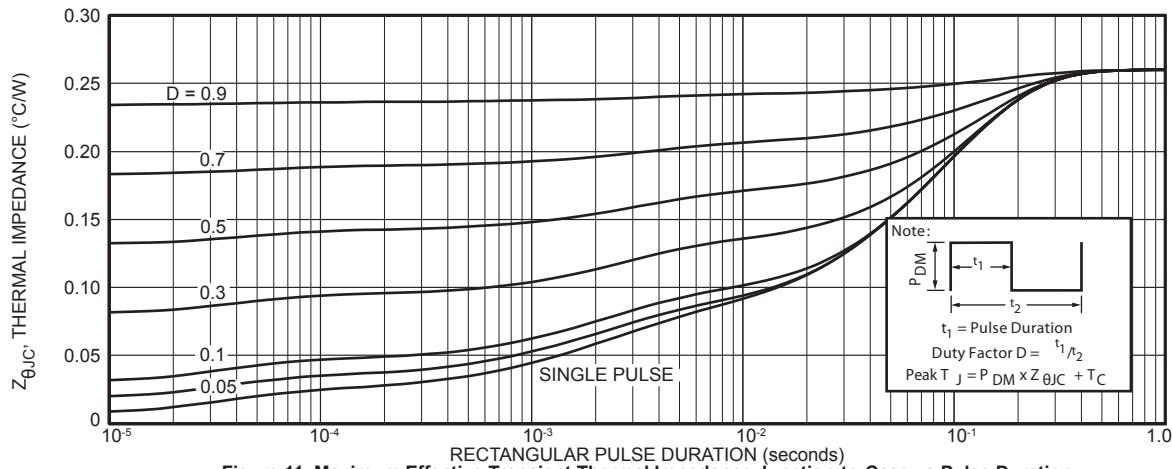
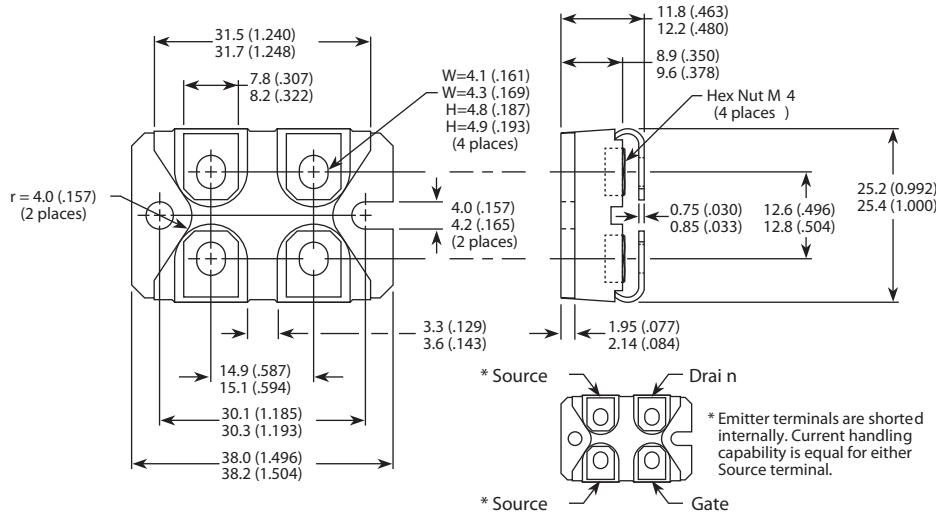


Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)